TF Semiconductor Solutions

Advance Info

TF21364M

3-Phase Half-Bridge Gate Driver

Features

- **Three floating high-side drivers in bootstrap operation to 600V**
- **200mA source / 350mA sink output current capability**
- **Outputs tolerant to negative transients, dV/dt immune**
- **Wide VCC operating range: 10V to 20V**
- **Non-inverting logic inputs, 3.3V capability**
- **Internal deadtime of 290ns to protect MOSFETs**
- **Matched prop delay for all channels**
- **Schmitt triggered logic inputs**
- **Cross conduction prevention logic**
- **Undervoltage lockout for all channels**
- **Overcurrent protection shuts down drivers**
- **Extended temperature range: -40°C to +125°C**

Applications

- 3-Phase Motor Inverter Driver
- White Goods - Air Conditioner, Washing Machine, Refrigerator
- Industrial Motor Inverter - Power Tools, Robotics
- General Purpose 3-Phase Inverter

Description

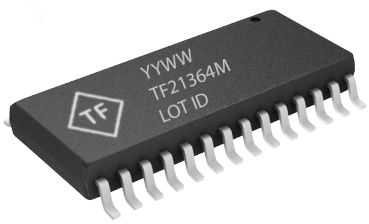
The TF21364M is a three-phase gate driver IC designed for high voltage, high speed applications, driving N-channel MOSFETs and IGBTs in a half-bridge configuration. TF Semiconductor's high voltage process enables the TF21364M high sides to switch to 600V in a bootstrap operation.

The TF21364M logic inputs are compatible with standard TTL and CMOS levels (down to 3.3V) to interface easily with controlling devices and are enabled low to better function in high noise environments. The driver outputs feature high pulse current buffers designed for minimum driver cross conduction.

The TF21364M offers numerous protection functions. A shoot-through protection logic prevents both outputs being high with both inputs high (fault state), an undervoltage lockout for V_{CC} shuts down all drivers through an internal fault control, and a UVLO for V_{BS} shuts down the respective high side output. Also an overcurrent protection will terminate the six outputs. Both the V_{CC} UVLO and the overcurrent protection trip an automatic fault clear with a timing that is adjustable with an external capacitor.

The TF21364M is offered in SOIC 28 package and operates over an extended -40 °C to +125 °C temperature range.

SOIC-28

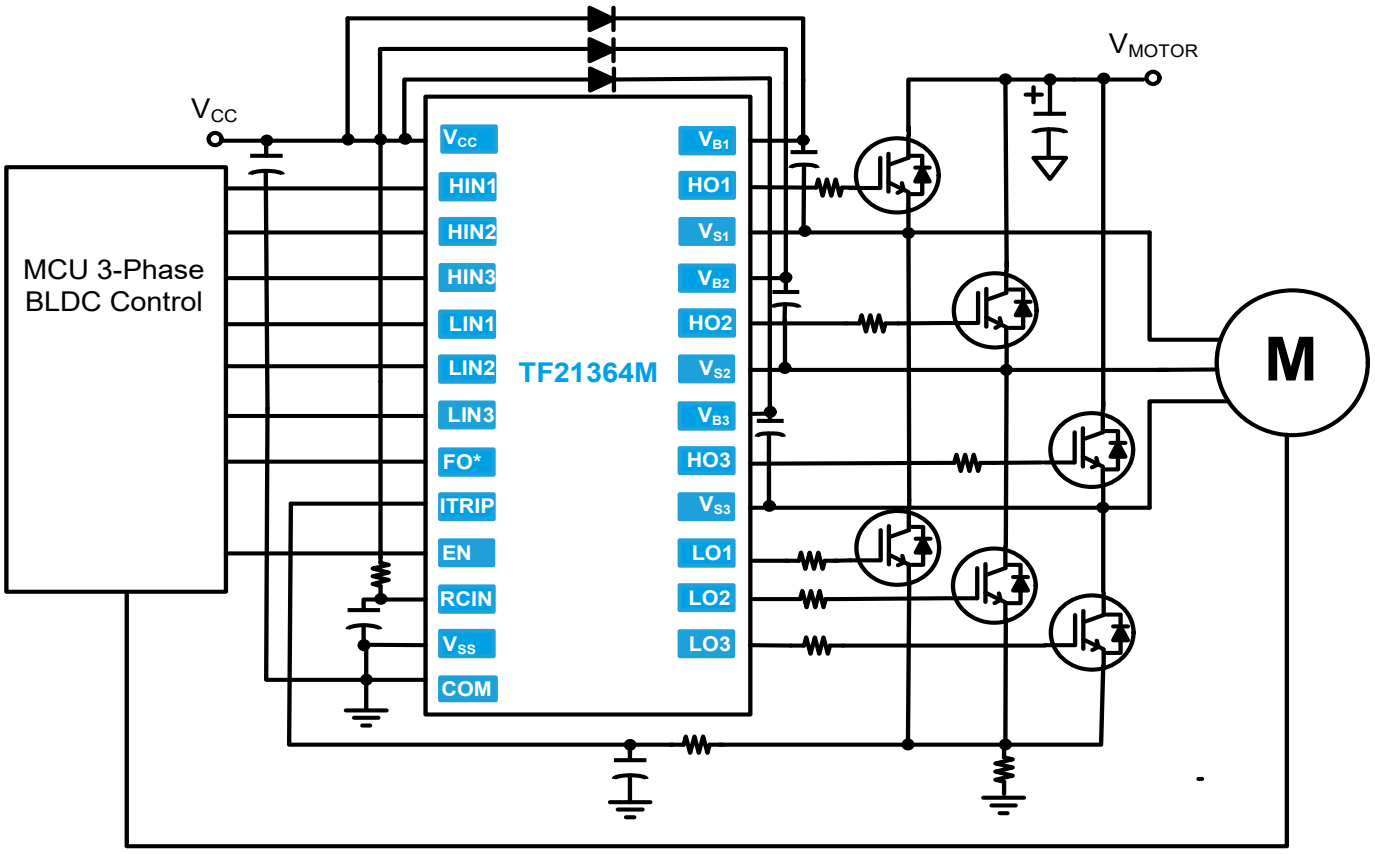


Ordering Information

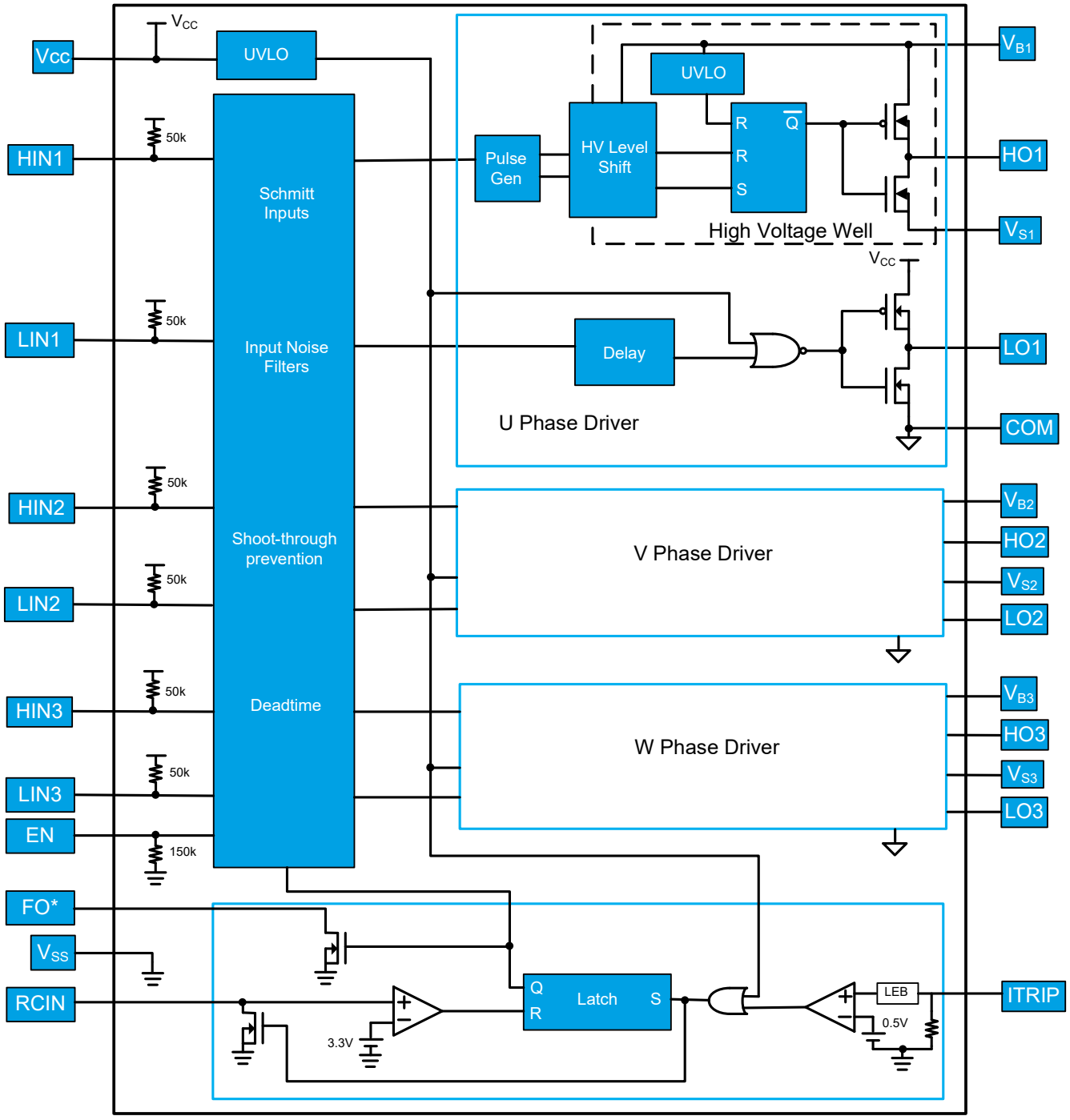
Year Year Week Week

PART NUMBER	PACKAGE	PACK / Qty	MARK
TF21364M-TLS	SOIC-28	Tube / 25	YYWW TF21364M Lot ID
TF21364M-TLH	SOIC-28	T&R / 1500	

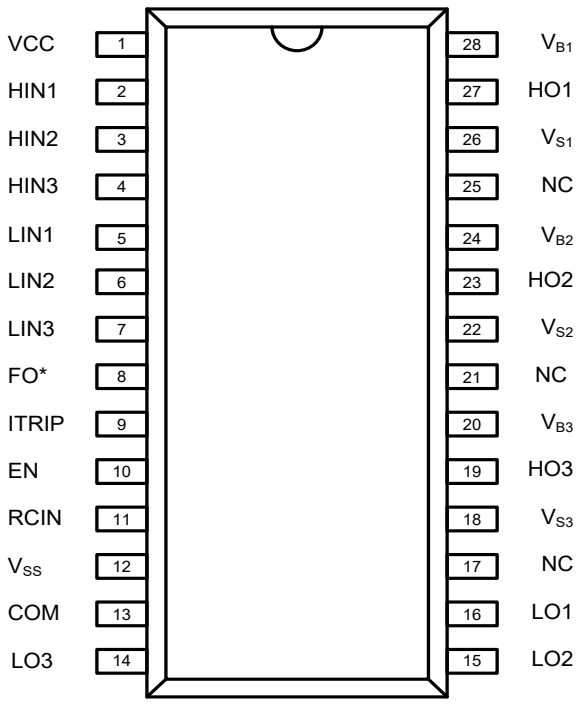
Typical Application



Functional Block Diagram



Pin Diagrams



Top View: SOIC-28

Pin Descriptions

PIN NAME	PIN NUMBER	PIN DESCRIPTION
VCC	1	Low-side and logic fixed supply
HIN1, HIN2, HIN3	2, 3, 4	Logic input for high-side gate driver output, in phase with HO.
LIN1, LIN2, LIN3	5, 6, 7	Logic input for low-side gate driver output, in phase with LO.
FO*	8	Fault output with open drain (fault with over-current and VCC UVLO)
ITRIP	9	Analog input for over-current shutdown
EN	10	Logic input for functionality, I/O logic functions when EN is high.
RCIN	11	An external RC network input used to define FAULT CLEAR delay
V_{SS}	12	Logic ground
COM	13	Low-side driver return
LO3, LO2, LO1	14, 15, 16	Low-side gate driver output
NC	17, 21, 25	No Connect
V_{S3},V_{S2},V_{S1}	18, 22, 26	High-side floating supply return
HO3, HO2, HO1	19, 23, 27	High-side gate driver output
V_{B3},V_{B2},V_{B1}	20, 24, 28	High-side floating supply

Absolute Maximum Ratings *(NOTE1)*

V_B - High-side floating supply voltage.....-0.3V to +624V
V_S - High-side floating supply offset voltage....V_B-24V to V_B+0.3V
V_{HO} - High-side floating output voltage.....V_S-0.3V to V_B+0.3V
V_{LO} - Low-side output voltage.....-0.3V to V_{CC}+0.3V
dV_S/dt - Offset supply voltage transient.....50 V/ns
V_{CC} - Low-side fixed supply voltage.....-0.3V to +24V
V_{IN} -Logic input voltage (HIN, LIN, ITRIP, EN and FO*).....-0.3V to 5.5V

NOTE1 *Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.*

P_D - Package power dissipation at $T_A \leq 25$ °C
SOIC-28.....2.3W

SOIC-28 Thermal Resistance ***(NOTE2)***
θ_{JC}.....45 °C/W
θ_{JA}.....60°C/W

T_J - Junction operating temperature.....+150 °C
T_L - Lead Temperature (soldering, 10 seconds).....+300 °C
T_{stg} - Storage temerature .....-55 to 150 °C

NOTE2 *Thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.*

Recommended Operating Conditions

Symbol	Parameter	MIN	MAX	Unit
V_B	High side floating supply absolute voltage	V_S + 10	V_S + 20	V
V_S	High side floating supply offset voltage	***NOTE3***	600	V
V_{HO}	High side floating output voltage	V_S	V_B	V
V_{CC}	Low side fixed supply voltage	10	20	V
V_{LO}	Low side output voltage	COM	V_{CC}	V
V_{IN}	Logic input voltage (HIN, LIN, ITRIP, EN)	V_{SS}	5	V
V_{FO}	Fault output Voltage	V_{SS}	V_{CC}	V
V_{SS}	Logic Ground	-5	5	C
T_A	Ambient temperature	-40	125	°C

NOTE3 *Logic operational for VS of -5V to +600V.*

DC Electrical Characteristics *(NOTE4)*

V_{BIAS} (V_{CC}, V_{BS}) = 15V, T_A = 25 °C , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
V_{IH}	Logic "1" input voltage		2.4			V
V_{IL}	Logic "0" input voltage				0.8	
V_{OH}	High level output voltage, V_{BIAS} - V_O	I_O = 0mA			0.1	
V_{OL}	Low level output voltage, V_O	I_O = 0mA			0.1	
I_{LK}	Offset supply leakage current	VB = VS = 600V			10	µA
I_{BSQ}	Quiescent V_{BS} supply current	V_{IN} = 0V or 5V, EN=0V	10	85	130	
I_{CCQ}	Quiescent V_{CC} supply current	V_{IN} = 0V or 5V, EN=0V		1.1	1.6	mA
I_{IN+}	Logic input bias current (HO=LO=HIGH)	V_{IN} = 5V		130	200	µA
I_{IN-}	Logic input bias current (HO=LO=LOW)	V_{IN} = 0V		3.0	20	
I_{EN+}	Logic Enable "1" input bias current	V_{EN} = 5V		33	80	µA
I_{EN-}	Logic Enable "0" input bias current	V_{EN} = 0V			2	µA
V_{BSUV+} V_{CCUV+}	V_{BS} and V_{CC} supply under-voltage positive going threshold		7.6	8.9	9.9	V
V_{BSUV-} V_{CCUV-}	V_{BS} and V_{CC} supply under-voltage negative going threshold		7.1	8.3	9.4	
I_{O+}	Output high short circuit pulsed current	V_O = 0V, PW ≤ 10 µs	120	200		mA
I_{O-}	Output low short circuit pulsed current	V_O = 15V, PW ≤ 10 µs	250	350		
V_{ITH+}	Overcurrent detect positive threshold		400	500	600	mV
V_{ITH-}	Overcurrent detect negative threshold		340	420	500	mV
I_{CSIN}	Short-circuit input current	V_{CSIN}=1V	6.0	11	16	µA
$V_{RCINTH+}$	RCIN Positive going threshold voltage		7.0	8.4	9.8	V
$V_{RCINTH-}$	RCIN Negative going threshold voltage			5		V
V_{FOL}	Fault output low level voltage	V_{CS}=1V, I_{FO}=1.5mA		0.2	0.5	V
R_{DSRCIN}	RCIN On resistance	I_{RCIN}=1.5mA	40	75	110	Ω
R_{DSFO}	Fault output on resistance	I_{FO}=1.5mA	80	130	180	Ω

NOTE4 *The V_{IN}, V_{TH}, and I_{IN} parameters are referenced to V_{SS} and are applicable to all six channels (HIN1,2,3 and LIN1,2,3). The V_O and I_O parameters are applicable to the outputs (HO1,2,3 and LO1,2,3 and are referenced to COM.*

AC Electrical Characteristics

V_{BIAS} (V_{CC}, V_{BS}) = 15V, C_L = 1000pF, and T_A = 25 °C , unless otherwise specified.

Symbol	Parameter	Conditions	MIN	TYP	MAX	Unit
t_{on}	Turn-on propogation delay	V_S = 0V	200	330	460	ns
t_{off}	Turn-off propogation delay	V_S = 0V	200	330	460	
t_r	Turn-on rise time	V_S = 0V		90	150	
t_f	Turn-off fall time			35	60	
t_{DM}	Delay matching				50	ns
t_{EN}	Enable low to output shutdown delay		225	330	425	ns
t_{BLT}	ITRIP Pin leading-edge blanking time		200	300	400	ns
t_{FLT}	Time from ITRIP triggering to FO*	From V_{ITRIP}= 1V to FO* turn off	360	550	760	ns
t_{ITRIP}	Time from ITRIP triggering to all gate outputs turn off	From V_{ITRIP}= 1V to starting gate turn off	420	615	820	ns
t_{FLTIN}	Input filtering time (HIN, LIN, EN)			250		ns
t_{FLTCLR}	Fault clear time	C_{RCIN} = 1nF, R_{RCIN} = 2MΩ		1.6		ms
t_{DT}	Deadtime		200	290	420	ns
t_{DTM}	Deadtime matching				50	ns
t_{PM}	Output pulse width matching (***NOTE5***)	PW_{IN} >1μs		50	75	ns

NOTE5 *t_{PM} is defined as PW_{IN} - PW_{OUT}.*

Timing Waveforms

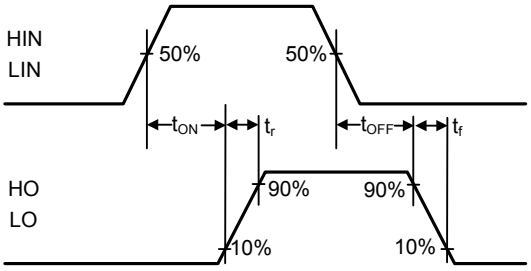


Figure 1. Switching Time Waveform Definitions

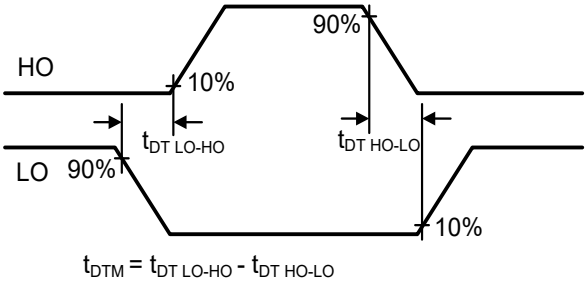


Figure 2. Deadtime Waveform Definitions

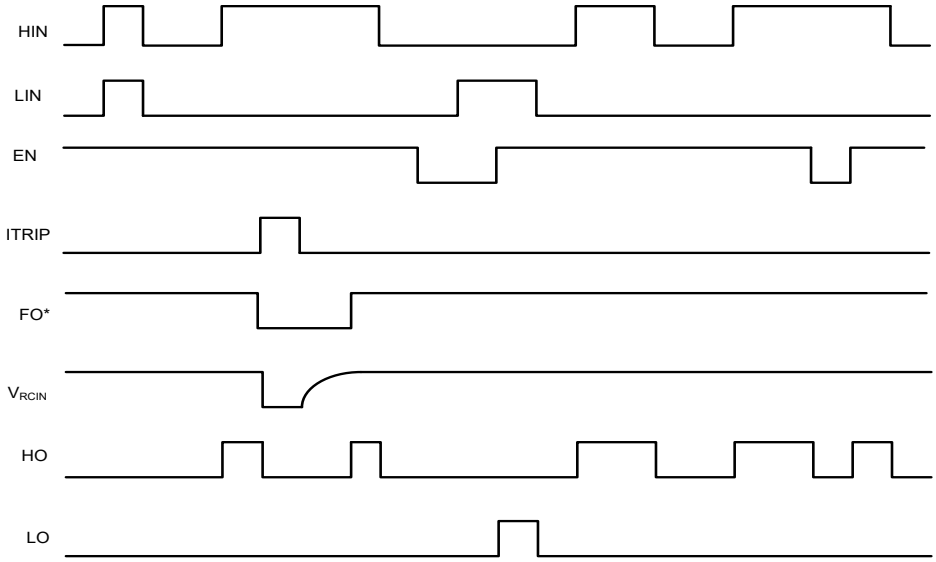


Figure 3. Input/Output Timing Diagram

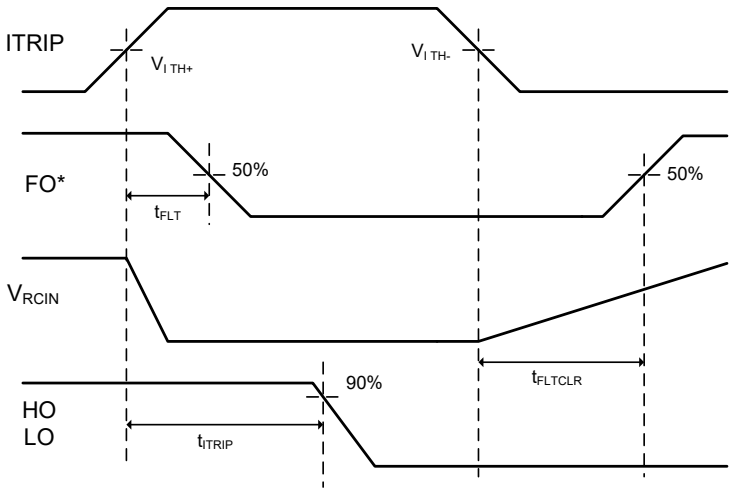
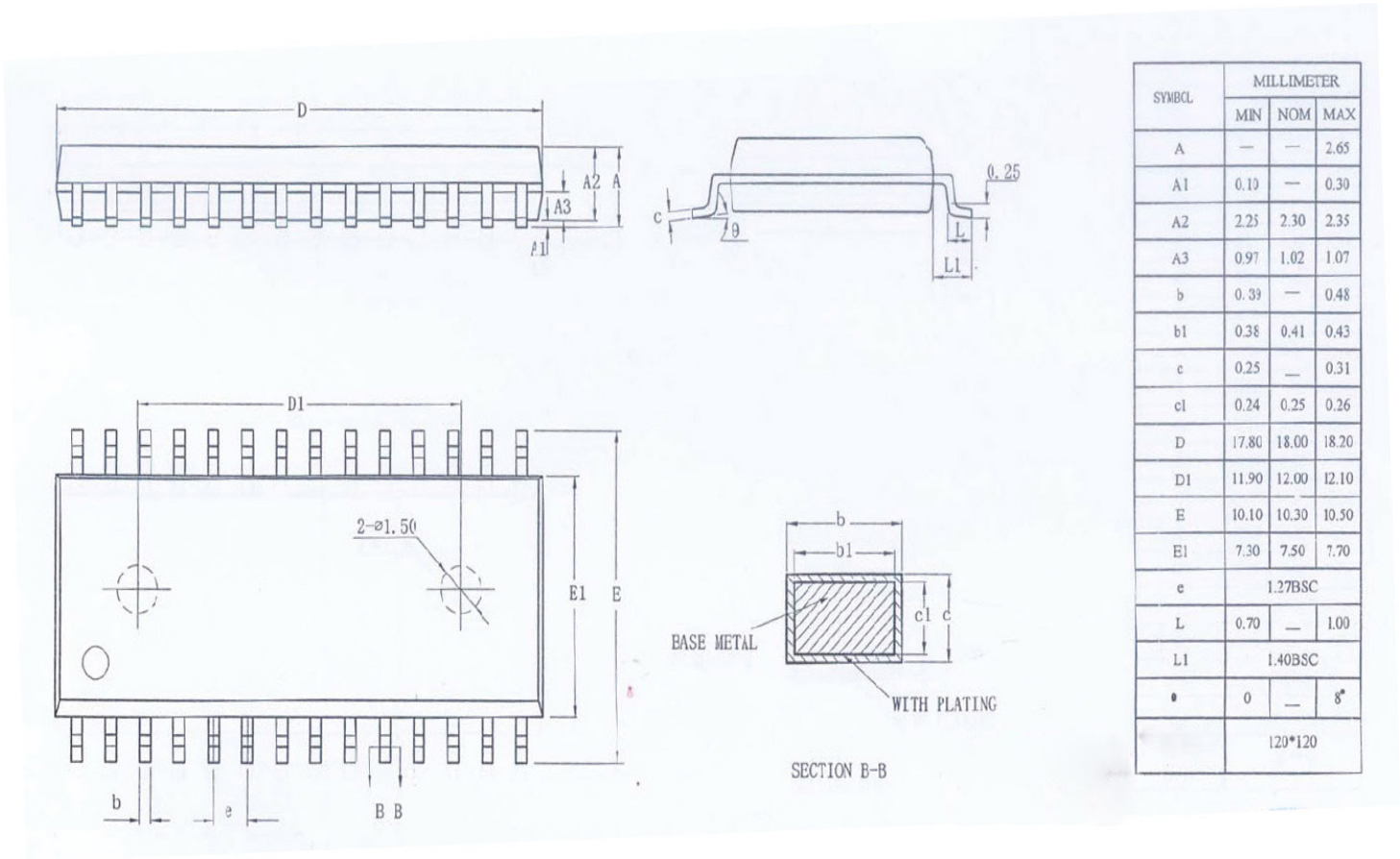


Figure 4. Overcurrent Timing Definitions

Package Dimensions (SOIC-28)

Please contact support@tfsemi.com for package availability.



SYMBOL	MILLIMETER		
	MIN	NOM	MAX
A	—	—	2.65
A1	0.10	—	0.30
A2	2.25	2.30	2.35
A3	0.97	1.02	1.07
b	0.39	—	0.48
b1	0.38	0.41	0.43
c	0.25	—	0.31
c1	0.24	0.25	0.26
D	17.80	18.00	18.20
D1	11.90	12.00	12.10
E	10.10	10.30	10.50
E1	7.30	7.50	7.70
e	1.27BSC		
L	0.70	—	1.00
L1	1.40BSC		
θ	0	—	8°
	120*120		

Revision History

Rev.	Change	Owner	Date
1.0	First release AI datasheet	Keith Spaulding	3/1/2019

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